FAIRCHILD SEMICONDUCTOR®

April 2008

FDMA510PZ

Single P-Channel PowerTrench® MOSFET
–20V, –7.8A, 30mΩ

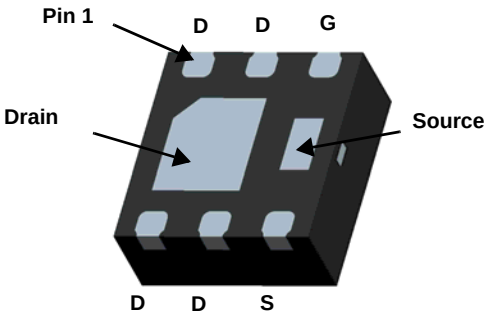
Features

- Max $r_{DS(on)}$ = 30mΩ at V_{GS} = –4.5V, I_D = –7.8A
- Max $r_{DS(on)}$ = 37mΩ at V_{GS} = –2.5V, I_D = –6.6A
- Max $r_{DS(on)}$ = 50mΩ at V_{GS} = –1.8V, I_D = –5.5A
- Max $r_{DS(on)}$ = 90mΩ at V_{GS} = –1.5V, I_D = –2.0A
- Low profile - 0.8mm maximum - in the new package MicroFET 2X2 mm
- HBM ESD protection level > 3KV typical (Note 3)
- RoHS Compliant

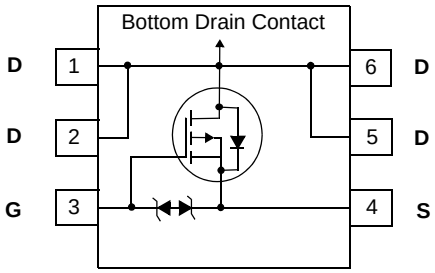
General Description

This device is designed specifically for battery charge or load switching in cellular handset and other ultraportable applications. It features a MOSFET with low on-state resistance.

The MicroFET 2X2 package offers exceptional thermal performance for its physical size and is well suited to linear mode applications.



MicroFET 2X2 (Bottom View)



MOSFET Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V_{DS}	Drain to Source Voltage		–20	V
V_{GS}	Gate to Source Voltage		±8	V
I_D	Drain Current -Continuous	(Note 1a)	–7.8	A
	-Pulsed		–24	
P_D	Power Dissipation	(Note 1a)	2.4	W
	Power Dissipation	(Note 1b)	0.9	
T_J, T_{STG}	Operating and Storage Junction Temperature Range		–55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	52	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	145	

Package Marking and Ordering Information

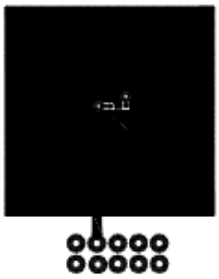
Device Marking	Device	Package	Reel Size	Tape Width	Quantity
510	FDMA510PZ	MicroFET 2X2	7”	8mm	3000units

Electrical Characteristics T_J = 25°C unless otherwise noted

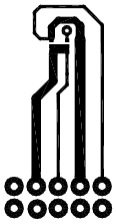
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = –250μA, V_{GS} = 0V	–20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = –250μA, referenced to 25°C		–13		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = –16V, V_{GS} = 0V			–1	μA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±8V, V_{DS} = 0V			±10	μA
On Characteristics						
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = –250μA	–0.4	–0.7	–1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = –250μA, referenced to 25°C		3		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = –4.5V, I_D = –7.8A		27	30	mΩ
		V_{GS} = –2.5V, I_D = –6.6A		34	37	
		V_{GS} = –1.8V, I_D = –5.5A		46	50	
		V_{GS} = –1.5V, I_D = –2.0A		60	90	
		V_{GS} = –4.5V, I_D = –7.8A ,T_J = 125°C		36	40	
g_{FS}	Forward Transconductance	V_{DD} = –5V, I_D = –7.8A		26		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = –10V, V_{GS} = 0V, f = 1MHz		1110	1480	pF
C_{oss}	Output Capacitance			205	275	pF
C_{rss}	Reverse Transfer Capacitance			185	280	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = –10V, I_D = –7.8A, V_{GS} = –4.5V, R_{GEN} = 6Ω		7	14	ns
t_r	Rise Time			9	18	ns
$t_{d(off)}$	Turn-Off Delay Time			125	200	ns
t_f	Fall Time			64	103	ns
Q_g	Total Gate Charge	V_{DD} = –5V, I_D = –7.8A, V_{GS} = –4.5V		19	27	nC
Q_{gs}	Gate to Source Charge			2.1		nC
Q_{gd}	Gate to Drain “Miller” Charge			4.2		nC
Drain-Source Diode Characteristics						
I_S	Maximum Continuous Drain-Source Diode Forward Current				–2	A
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0V, I_S = –2A		–0.8	–1.2	V
t_{rr}	Reverse Recovery Time	I_F = –7.8A, di/dt = 100A/μs		66	106	ns
Q_{rr}	Reverse Recovery Charge			44	71	nC

Notes:

1. $R_{\theta JA}$ is determined with the device mounted on a 1in^2 pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. 52°C/W when mounted on a 1 in^2 pad of 2 oz copper.



b. 145°C/W when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300μs, Duty cycle < 2.0%.
3. The diode connected between the gate and source serves only as protection against ESD. No gate overvoltage rating is implied.

Typical Characteristics T_J = 25°C unless otherwise noted

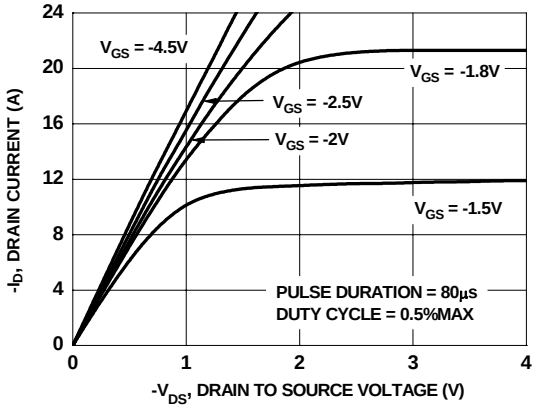


Figure 1. On-Region Characteristics

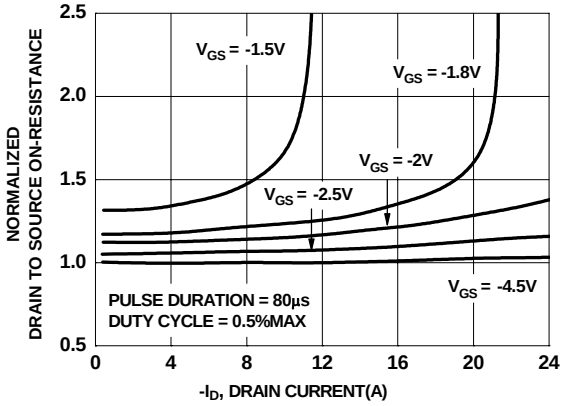


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

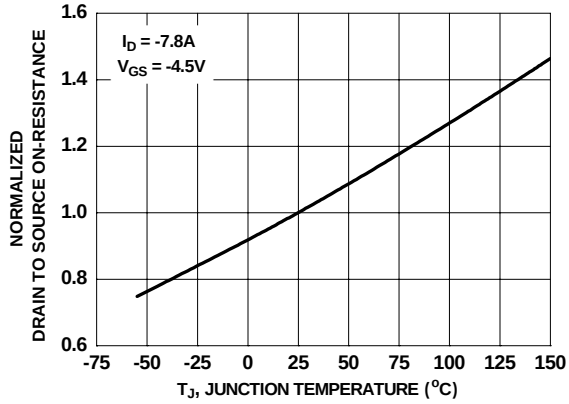


Figure 3. Normalized On-Resistance vs Junction Temperature

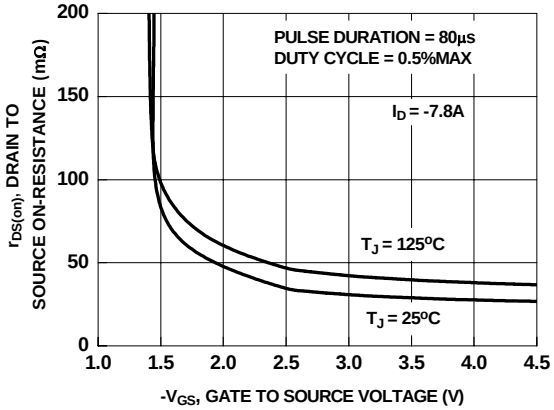


Figure 4. On-Resistance vs Gate to Source Voltage

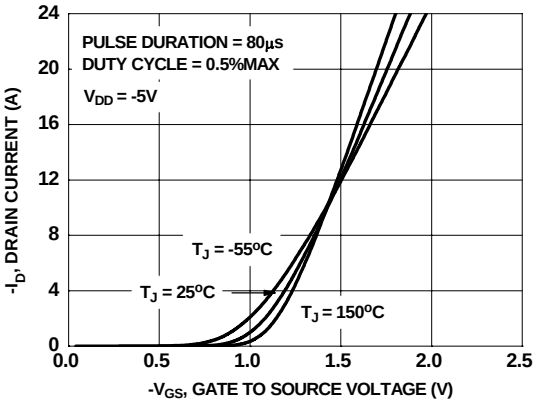


Figure 5. Transfer Characteristics

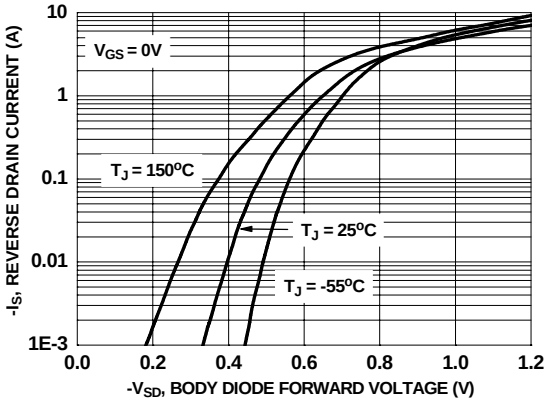


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics T_J = 25°C unless otherwise noted

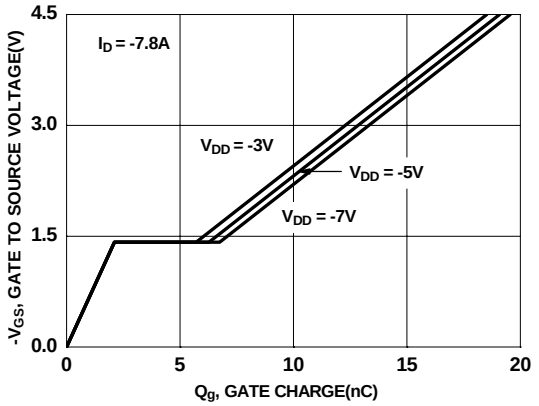


Figure 7. Gate Charge Characteristics

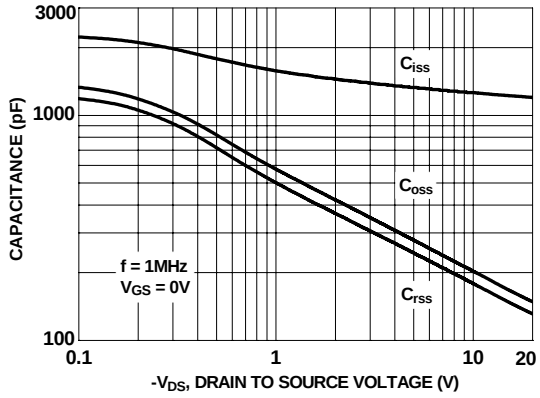


Figure 8. Capacitance vs Drain to Source Voltage

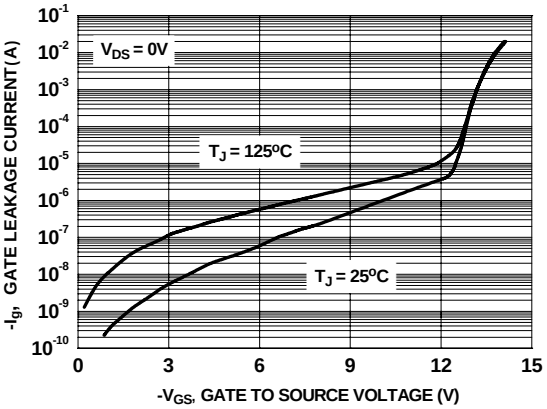


Figure 9. Gate Leakage Current vs Gate to Source Voltage

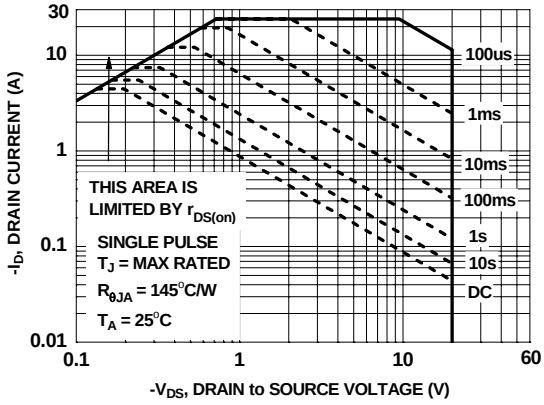


Figure 10. Forward Bias Safe Operating Area

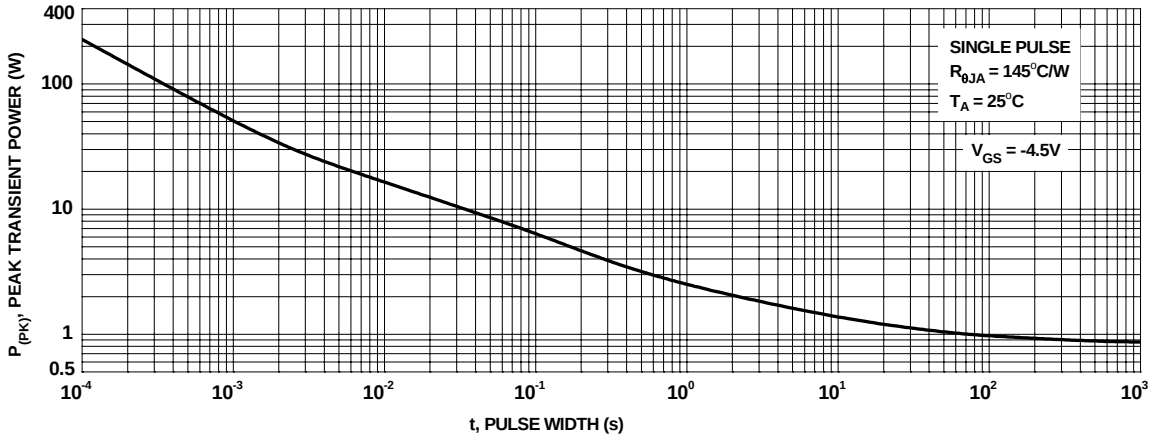


Figure 11. Single Pulse Maximum Power Dissipation

Typical Characteristics T_J = 25°C unless otherwise noted

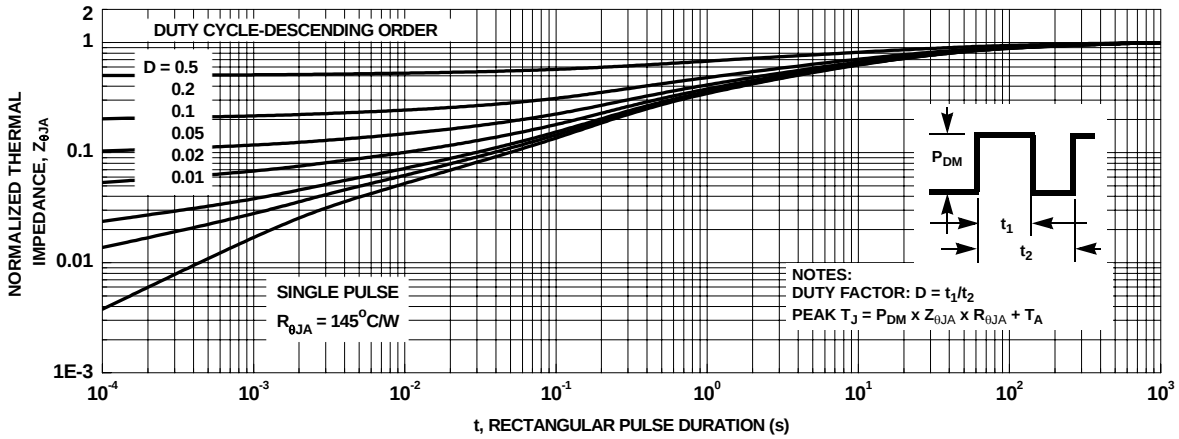
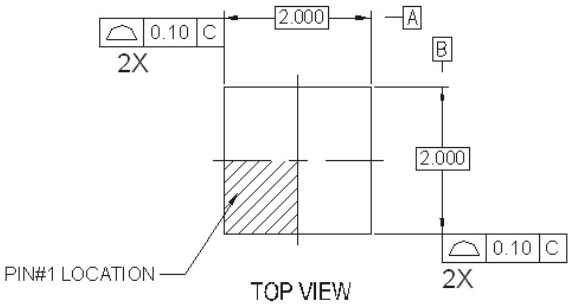
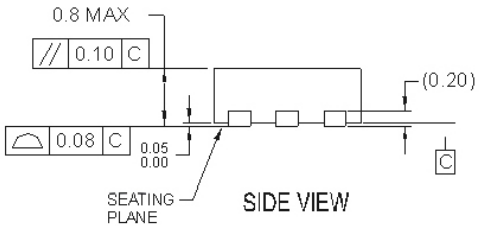


Figure 12. Transient Thermal Response Curve

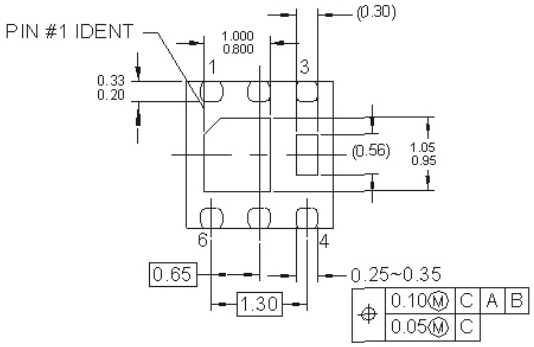
Dimensional Outline and Pad Layout



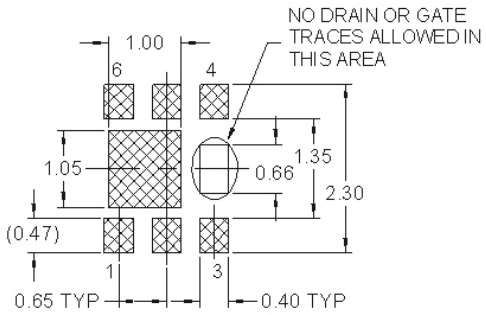
TOP VIEW



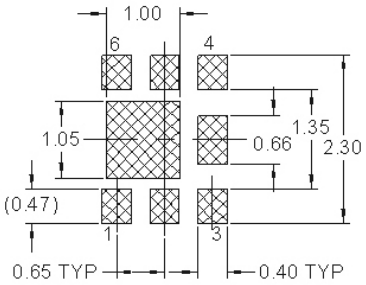
SIDE VIEW



BOTTOM VIEW



RECOMMENDED LAND PATTERN OPT 1



RECOMMENDED LAND PATTERN OPT 2

NOTES:

A. DOES NOT FULLY CONFORM TO JEDEC REGISTRATION MO-229 DATED AUG/2003
B. DIMENSIONS ARE IN MILLIMETERS.
C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994
D. DRAWING FILENAME: MKT-MLP06Lrev2.

FAIRCHILD SEMICONDUCTOR®

TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidianries, and is not intended to be an exhaustive list of all such trademarks.

ACEx®
Build it Now™
CorePLUS™
CorePOWER™
CROSSVOLT™
CTL™
Current Transfer Logic™
EcoSPARK®
EfficentMax™
EZSWITCH™ *
™
®
Fairchild®
Fairchild Semiconductor®
FACT Quiet Series™
FACT®
FAST®
FastvCore™
FlashWriter® *
FPS™
F-PFS™
FRFET®
Global Power Resource℠
Green FPS™
Green FPS™ e-Series™
GTO™
IntelliMAX™
ISOPLANAR™
MegaBuck™
MICROCOUPLER™
MicroFET™
MicroPak™
MillerDrive™
MotionMax™
Motion-SPM™
OPTOLOGIC®
OPTOPLANAR®
®
PDP-SPM™
Power-SPM™
PowerTrench®
Programmable Active Droop™
QFET®
QS™
Quiet Series™
RapidConfigure™
Saving our world 1mW at a time™
SmartMax™
SMART START™
SPM®
STEALTH™
SuperFET™
SuperSOT™-3
SuperSOT™-6
SuperSOT™-8
SuperMOS™
SYSTEM GENERAL ®
The Power Franchise®
the power franchise
TinyBoost™
TinyBuck™
TinyLogic®
TINYOPTO™
TinyPower™
TinyPWM™
TinyWire™
µSerDes™
µSerDes
UHC®
Ultra FRFET™
UniFET™
VCX™
VisualMax™

* EZSWITCH™ and FlashWriter® are trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	This datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. I34